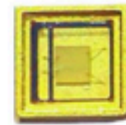


GaN系列紫外探测器 LD-G360-100S

UVA Sensor: LD-G360-100S

Features

Indium Gallium nitride based material
 Broad band UVA+UVB+UVC photodiode
 Photovoltaic mode operation
 SMD3535 package
 Good visible blindness
 High responsivity and low dark current



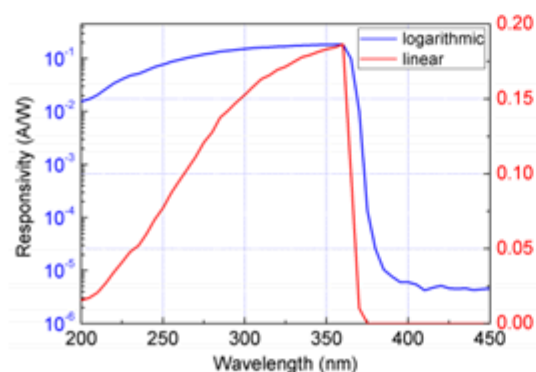
Applications

UV LED monitoring
 UV radiation dose measurement
 UV Curing

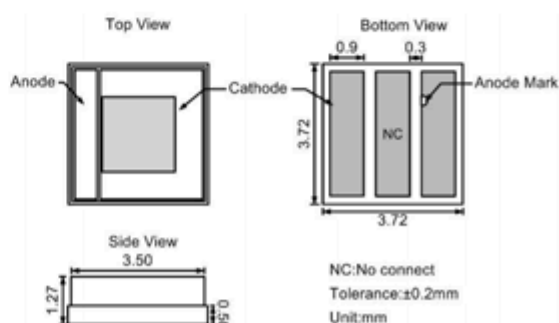
Specifications

Parameter	Symbol	Value	Unit
Spectral characteristics (25 °C)			
Wavelength of peak responsivity	λ_{\max}	360	nm
Peak responsivity (at 360 nm)	R_{\max}	0.18	A/W
Spectral response range	-	180~370	nm
UV/visible rejection ratio ($R_{\max}/R_{400\text{ nm}}$)	VB	$>10^4$	-
General characteristics (25 °C)			
Chip size	A	1	mm ²
Dark current (1 V reverse bias)	I_d	<1	nA
Capacitance (at 0 V and 1 MHz)	C	23	pF
Temperature coefficient	T_c	-0.1	%/°C
Maximum ratings			
Operation temperature range	T_{opt}	-40~85	°C
Storage temperature range	T_{stor}	-40~85	°C
Soldering temperature (3 s)	T_{sold}	260	°C
Reverse voltage	$V_{R_{\max}}$	10	V

Spectral response



Package dimensions



***Caution:** ESD can damage the device hence please avoid ESD.